

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) ~~An electro-optical device comprising, above a substrate:~~  
device, comprising:

a substrate;

a data line extending in a first direction;

a scanning line extending in a second direction and intersecting the data line;

a pixel electrode and a thin film transistor disposed so as to correspond to an intersection region of the data line and the scanning ~~line;~~ line, the pixel electrode being formed above the substrate;

a storage capacitor electrically connected to the thin film transistor and the ~~pixel-electrode;~~ electrode, the storage capacitor being disposed above the substrate and below the pixel electrode; and

a shielding layer disposed ~~between~~ above the data line and below the pixel electrode,

a nitride film being included in the shielding layer and being formed along the data line and wider than the data line.

2. (Previously Presented) The electro-optical device according to Claim 1, a planarization process being performed on a surface of an interlayer insulating film arranged as a base of the pixel electrode.

3. (Previously Presented) The electro-optical device according to Claim 1, the data line being formed of the same film as one of a pair of electrodes which constitute a storage capacitor.

4. (Previously Presented) The electro-optical device according to Claim 3, the data line forming a laminated structure of an aluminum film and a conductive polysilicon film.

5. (Previously Presented) The electro-optical device according to Claim 1, further comprising:

a relay layer being electrically connected to the pixel electrode and one of a pair of electrodes which constitute a storage capacitor.

6. (Previously Presented) The electro-optical device according to Claim 5, the relay layer being made of an aluminum film and a nitride film.

7. (Previously Presented) The electro-optical device according to Claim 5, the shielding layer being formed of the same film as the relay layer.

8. (Previously Presented) The electro-optical device according to Claim 1, the nitride film being formed on a surface of the data line.

9-17. (Canceled)

18. (Currently Amended) The electro-optical device according to Claim 1, the shielding layer being formed of a transparent conductive material and being formed over an entire surface of the substrate.

19-20. (Canceled)

21. (Currently Amended) An electronic apparatus having an electro-optical device comprising, ~~above a substrate:~~ device, comprising:

a substrate;

a data line extending in a first direction;

a scanning line extending in a second direction and intersecting the data line;

a pixel electrode and a thin film transistor disposed so as to correspond to an intersection region of the data line and the scanning line, the thin film transistor including a semiconductor ~~layer;~~ layer, the pixel electrode being formed above the substrate;

a storage capacitor electrically connected to the thin film transistor and the ~~pixel-electrode;~~ electrode, the storage capacitor being disposed above the substrate and below the pixel electrode;

a relay layer electrically connected with the pixel electrode;

a first contact hole electrically connecting the semiconductor layer of the thin film transistor with the data line;

a second contact hole electrically connecting the semiconductor layer of the thin film transistor with the relay layer; and

a shielding layer disposed ~~between~~ above the data line and below the pixel electrode,

a nitride film being included in the shielding layer and being formed along the data line and wider than the data line, the shielding layer being formed to cover the first contact hole and the second contact hole as viewed in plan.

22. (New) The electro-optical device according to claim 1, the shielding layer being applied with a fixed voltage.